

TDE1747 TDF1747

INTERFACE CIRCUIT - RELAY AND LAMP - DRIVER

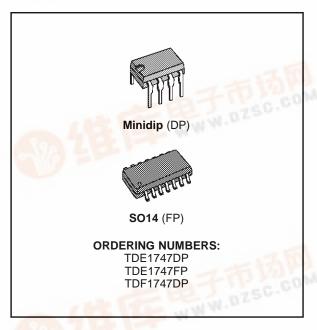
- OPEN GROUND PROTECTION
- HIGH OUTPUT CURRENT
- ADJUSTABLE SHORT-CIRCUIT PROTEC-TION TO GROUND
- THERMAL PROTECTION WITH HYSTERE-SIS TO AVOID THE INTERMEDIATE OUT-PUT LEVELS
- LARGE SUPPLY VOLTAGE RANGE: + 10 V TO + 45 V
- SHORT-CIRCUIT PROTECTION TO VCC

DESCRIPTION

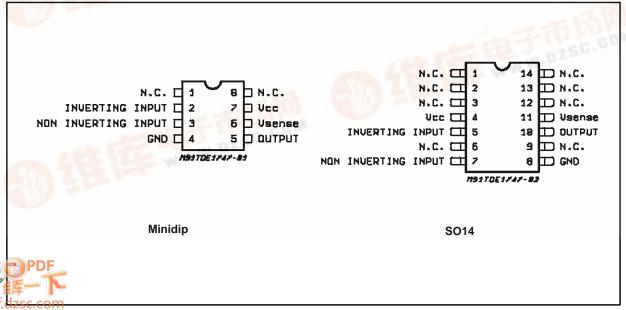
The TDE/TDF1747 is a monolithic comparator designed for high current and high voltage applications, specifically to drive lamps, relays, stepping motors.

These device is essentially blow-out proof. Current limiting is available to limit the peak output current to safe values, the adjustment only requires one external resistor. In addition, thermal shut down is provided to keep the I.C. from overheating. If internals dissipation becomes too great, the driver will shut down to prevent excessive heating. TDE1747 has an open ground protection. The output is also protected from short-circuits with the positive power supply.

PIN CONNECTIONS (Top view)



The device operates over a wide range of supply voltages from standard \pm 15 V operational amplifier supplies down to the single + 12 V or + 24 used for industrial electronic systems.



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TDE1747 - TDF1747

ABSOLUTE MAXIMUM RATINGS

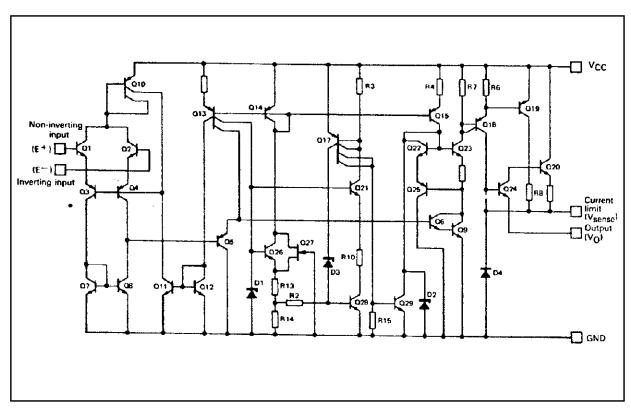
Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	50 *	V
V_{ID}	Differantial Input Voltage	50	V
Vı	Input Voltage	50	V
lo	Output Current	1	А
P _{tot}	Power Dissipation (T _{amb} = + 25 °C)	Internally Limited	W
T _{stg}	Storage Temperature Range	- 65 to + 150	°C
T _{oper}	Operating Ambient Temperature Range TDE1747 TDF1747	- 25 to + 85 - 40 to + 85	၁° ၁°

^{(*) 60}V, tâ 10ms

THERMAL CHARACTERISTICS

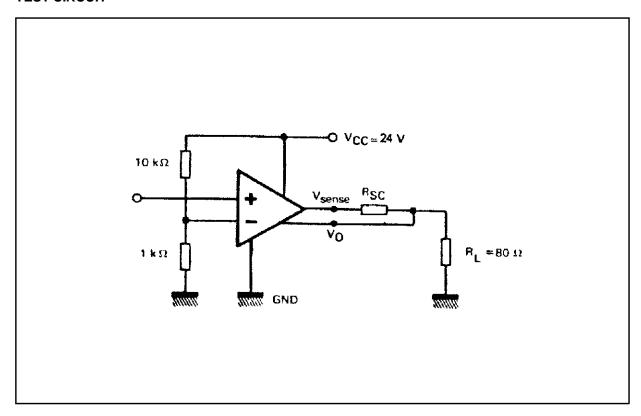
Symbol	Parameter		Value	Unit
R _{th(j-c)}	Maximum Junction-case Thermal Resistance		50	°C/W
R _{th(j-a)}	Maximum Junction-ambient Thermal Resistance		120	°C/W
Rth	Junction-ceramic Substrate (case glued to substrate)	SO14	90	°C/W
R _{th}	Junction-ceramic Substrate (case glued to substrate, substrate temperature maintened constant) SO14		65	°C/W

SCHEMATIC DIAGRAM

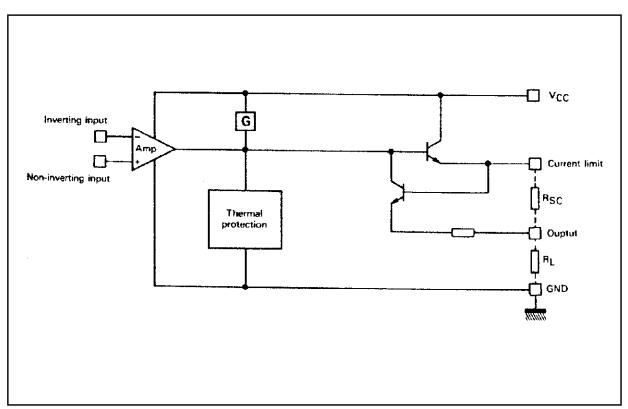


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TEST CIRCUIT



SIMPLIFIED CIRCUIT



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ELECTRICAL CHARACTERISTICS $T_j = -25$ to +85 °C, $V_{CC} = 8$ to 45 V, unless otherwise specified (note 1).

Symbol	Parameter	Min.	Тур.	Max.	Unit
V _{IO}	Input Offset Voltage - (note 2)	_	2	50	mV
I _{IB}	Input Bias Current	_	0.1	1.5	mA
lcc	Supply Current (V _{CC} = + 24 V, I _O = 0) High Level Low Level	_ 	4 2	6 4	mA mA
V _{I(max)}	Common-mode Input Voltage Range	2	_	V _{CC} -2	V
I _{SC}	Short-circuit Current Limit (T_{amb} = + 25 °C, V_{CC} = + 24) R_{SC} = 1.5 Ω TDE1747 R_{SC} = ∞	- 1	480 35	- 50	mA mA
V _{CC} -V _O	Output Saturation Voltage (output high) ($R_{SC} = 0$, V_{I} + $-V_{I}$ - ≥ 50 mV) $I_{O} = 300$ mA, $T_{j} = +25$ °C $T_{j} = +150$ °C	_	1.15 1.05	1.4 1.3	V
loL	Low Level Output Current $(V_O = 0, V_{CC} = +24 \text{ V})$ $T_j = +25 \text{ °C}$	_	0.01	10	μΑ

Notes:

Figure 1: Available Output Current vs. Limiting Resistor

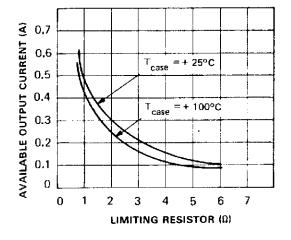
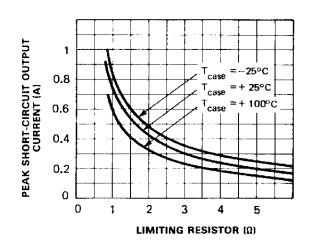


Figure 2: Peak Short-circuit Output Current vs. Limiting Resistor



¹⁾ For operating at high temperature, the TDE/TDF1747, must be derated based on a + 150 C maximum junction temperature and a junction-ambient thermal resistance of 120 °C/W for Minidip and 100 °C/W for the SO14.

²⁾ The offset voltage given is the maximum value of input voltage required to drive the output voltage within 2 V of the ground or the supply voltage.

Figure 3: Short-circuit Current vs. Case Temperature

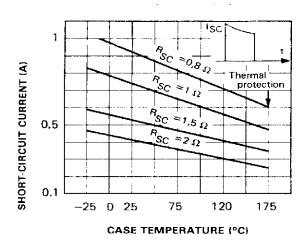


Figure 5: Output Current vs. Output Saturation Voltage

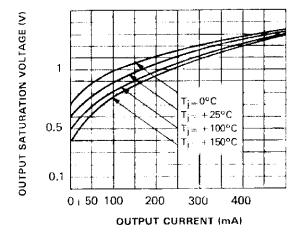


Figure 7: Supply Current vs. Junction Temperature

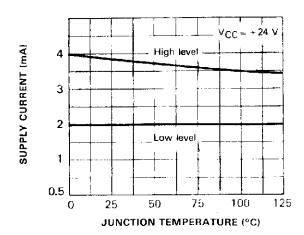


Figure 4: Minimum Limiting Resistor Value vs. Supply Voltage

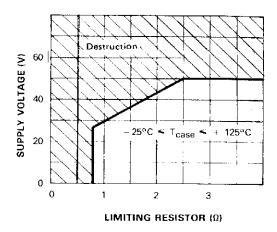


Figure 6: Supply Current vs. Supply Voltage

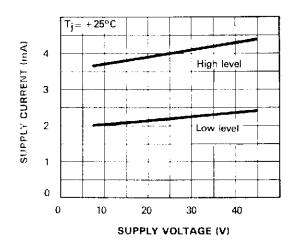


Figure 8: Safe Operating Area (non repetitive surge)

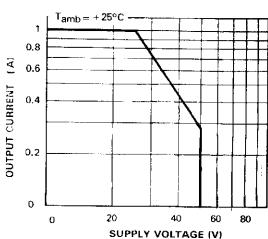
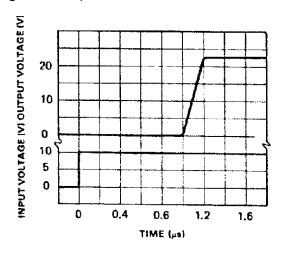
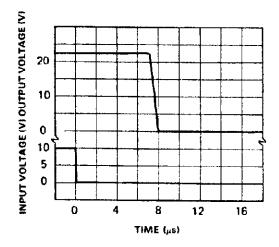


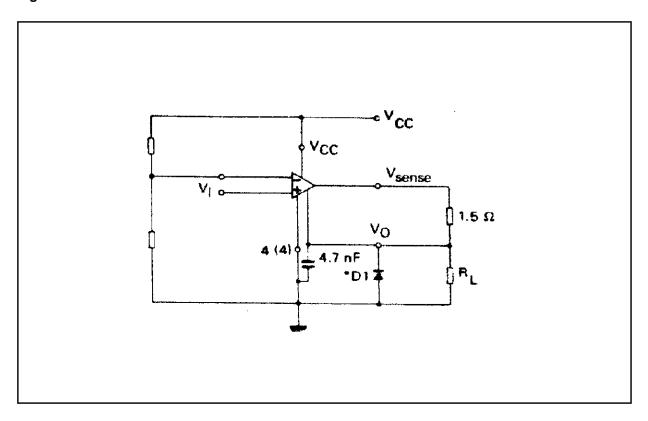
Figure 9: Response Time





TYPICAL APPLICATIONS

Figure 10: Base Circuit



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Figure 11: Output Current Extension (5A)

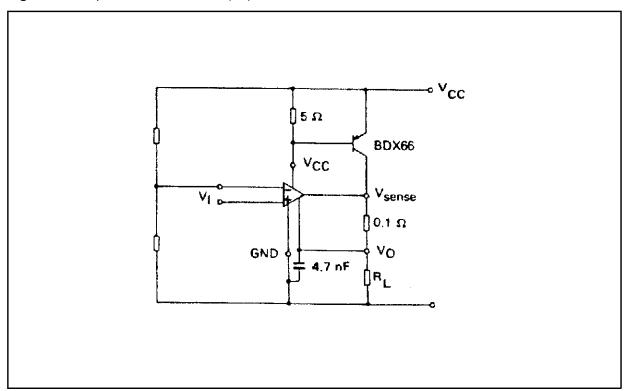
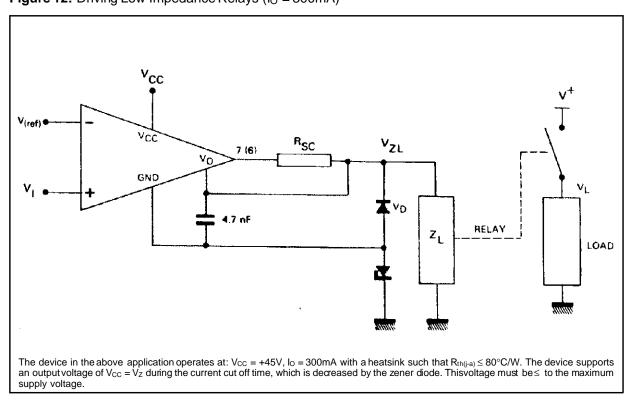
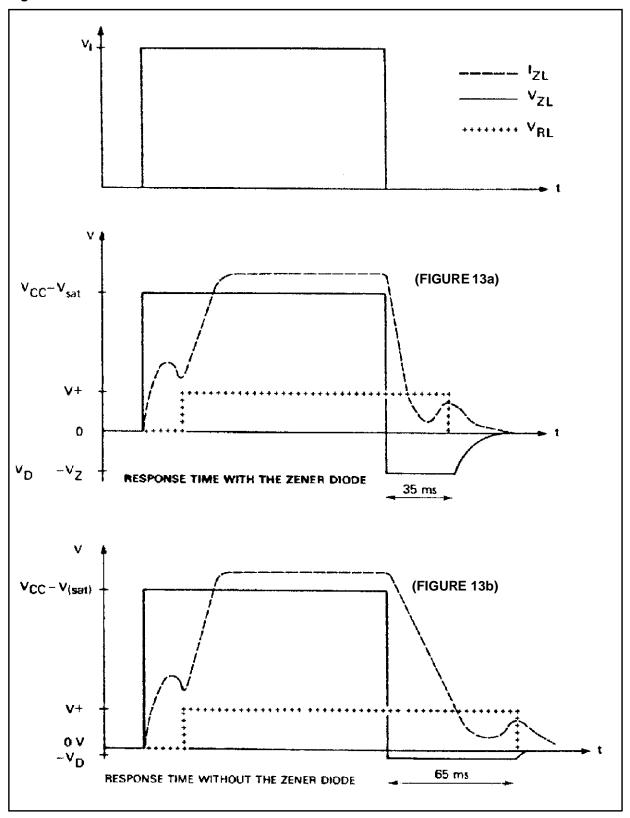


Figure 12: Driving Low Impedance Relays (I_O = 300mA)



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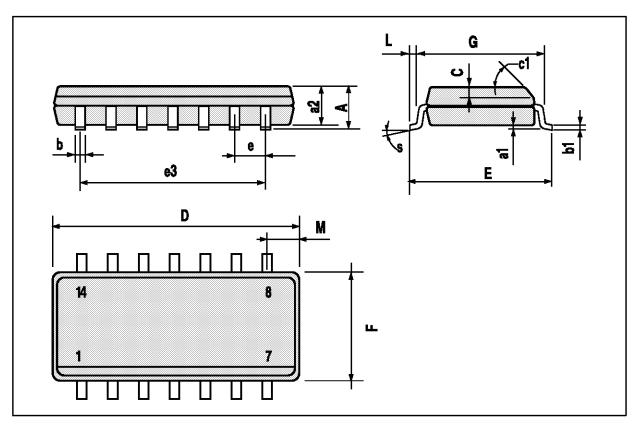
Figure 13: Waveforms



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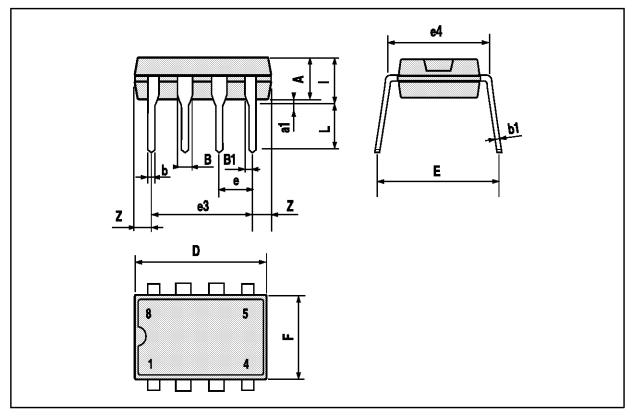
SO14 PACKAGE MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α			1.75			0.069
a1	0.1		0.25	0.004		0.009
a2			1.6			0.063
b	0.35		0.46	0.014		0.018
b1	0.19		0.25	0.007		0.010
С		0.5			0.020	
c1			45	(typ.)		
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
е		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.15		0.157
L	0.4		1.27	0.016		0.050
М			0.68			0.027
S	8 (max.)					



MINIDIP PACKAGE MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α		3.32			0.131	
a1	0.51			0.020		
В	1.15		1.65	0.045		0.065
b	0.356		0.55	0.014		0.022
b1	0.204		0.304	0.008		0.012
D			10.92			0.430
Е	7.95		9.75	0.313		0.384
е		2.54			0.100	
e3		7.62			0.300	
e4		7.62			0.300	
F			6.6			0.260
I			5.08			0.200
L	3.18		3.81	0.125		0.150
Z			1.52			0.060



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